



WANSEMI
万芯半导体

WP3040DP3

Enhancement Mode Dual N-Channel Power MOSFET

PDFN3x3/NMOS/30V/ ± 20 V/1.8V/22A/10m Ω

Rev0.6

30V, 10mΩ, 22A, Dual N-Channel

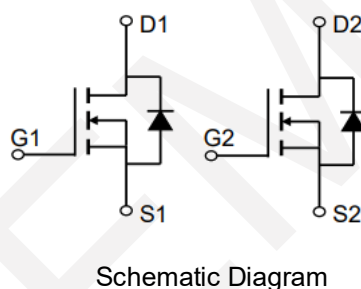
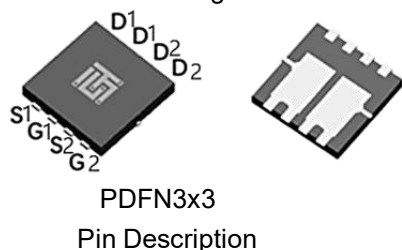
1.Features

- ◆ 30V MOSFET technology
- ◆ Low on-state resistance
- ◆ Fast switching
- ◆ $V_{GS} \pm 20V$

V_{DS}	$R_{DS(on)}$ Typ.	I_D Max.
30V	10mΩ @ 10V	22A
	14.5mΩ @ 4.5V	

2.Applications

- ◆ Power Switching Application
- ◆ Load Switching



3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WP3040DP3	WP3040DP3	PDFN3x3	5,000	50,000

4.Absolute Max Ratings at $T_a=25^\circ C$ (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V_{DSS}	30	V
Gate to Source Voltage	V_{GSS}	± 20	V
Drain Current (DC)	I_D	22	A
Drain Current (Pulse), $PW \leq 300\mu s$	I_{DP}	88	A
Total Dissipation	P_D	34	W
Avalanche Energy, Single Pulsed	E_{AS}	30	mJ
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

5. Thermal Resistance Ratings (Note 2)

Parameter	Symbol	Value	Unit
Junction to case	$R_{\theta JC}$	3.7	$^{\circ}\text{C/W}$
Junction to Ambient	$R_{\theta JA}$	59	$^{\circ}\text{C/W}$

Note 2: When mounted on 1 inch square copper board $t \leq 10\text{sec}$ The value in any given application depends on the user's specific board design.

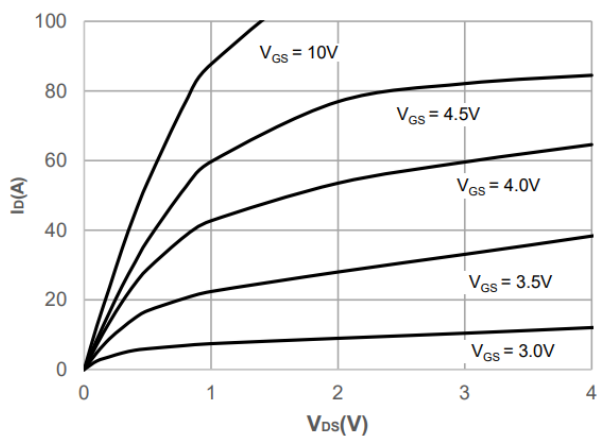
6. Electrical Characteristics at $T_a=25^{\circ}\text{C}$ (Note 3)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$			1.0	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{DS}=250\mu\text{A}$	1.0	1.8	2.5	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = 20\text{A}$, $V_{GS} = 10\text{V}$		10	13	$\text{m}\Omega$
		$I_D = 20\text{A}$, $V_{GS} = 4.5\text{V}$		14.5	17	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, Frequency=1.0MHz		1002		pF
Output Capacitance	C_{oss}			131		pF
Reverse Transfer Capacitance	C_{rss}			105		pF
Turn-ON Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{V}$, $I_{DS} = 30\text{A}$, $V_{GS} = 10\text{V}$, $R_G = 3\Omega$		6		ns
Rise Time	t_r			9		ns
Turn-OFF Delay Time	$t_{d(off)}$			22		ns
Fall Time	t_f			5		ns
Total Gate Charge	Q_g	$V_{DS} = 15\text{V}$, $V_{GS} = 0 \text{ to } 10\text{V}$, $I_{DS} = 30\text{A}$		20		nC
	Q_{gs}			4		nC
	Q_{gd}			5		nC
Diode Forward Voltage	V_{FSD}	$I_S = 20\text{A}$, $V_{GS} = 0\text{V}$		0.85	1.2	V

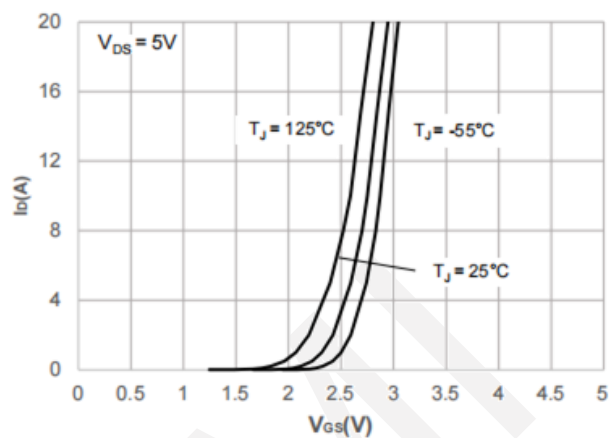
Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. Typical electrical and thermal characteristics

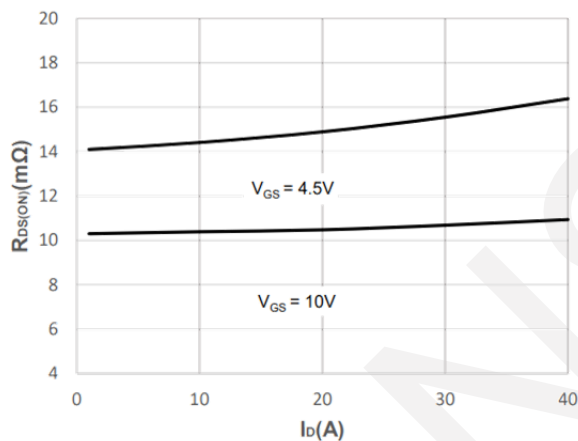
Figure 1: Output Characteristics



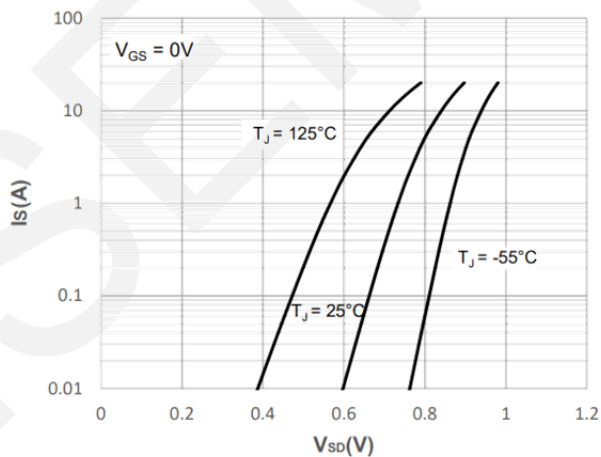
Output Characteristics



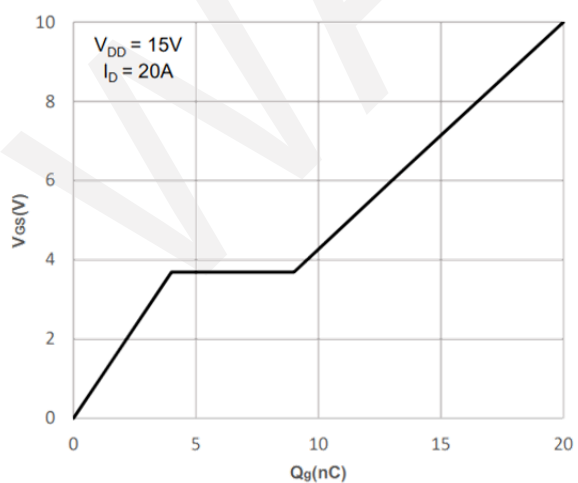
Typical Transfer Characteristics



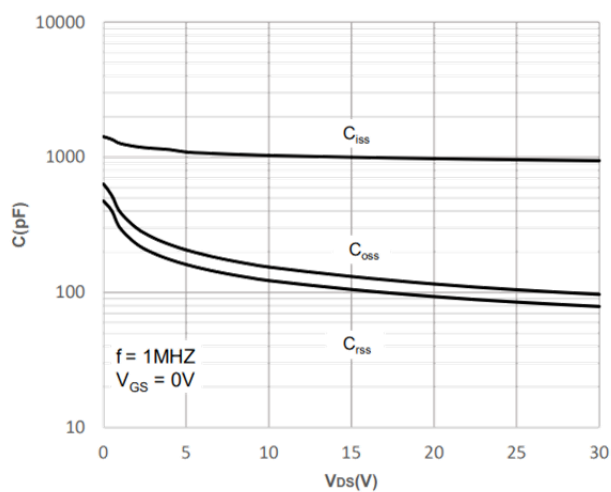
On-resistance vs. Drain Current



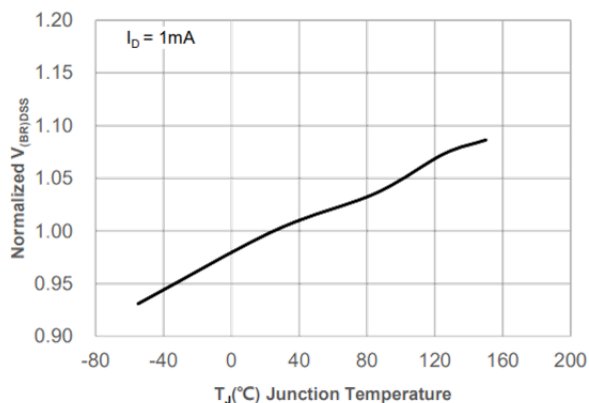
Body Diode Characteristics



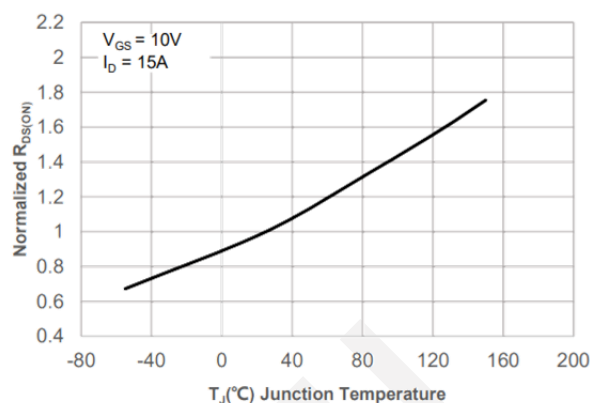
Gate Charge Characteristics



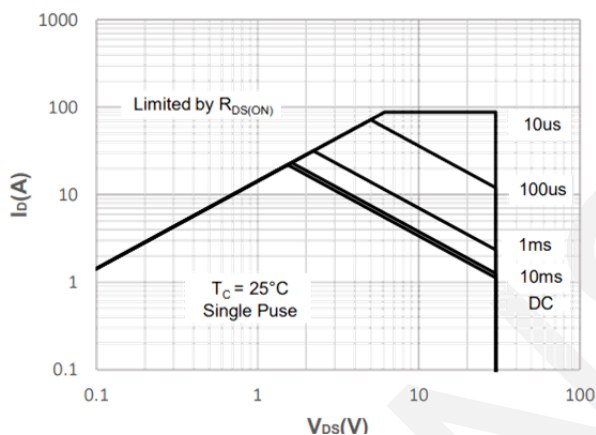
Capacitance Characteristics



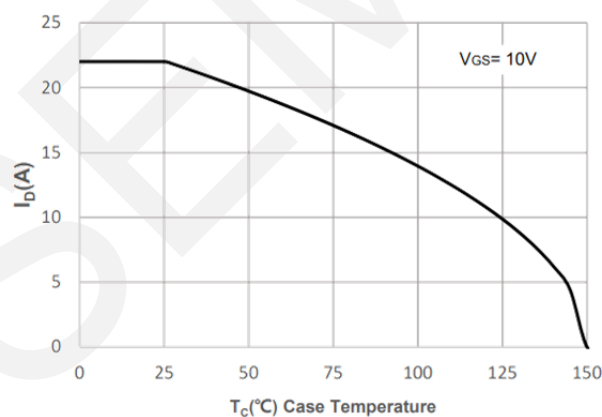
Normalized Breakdown Voltage vs.
Junction Temperature



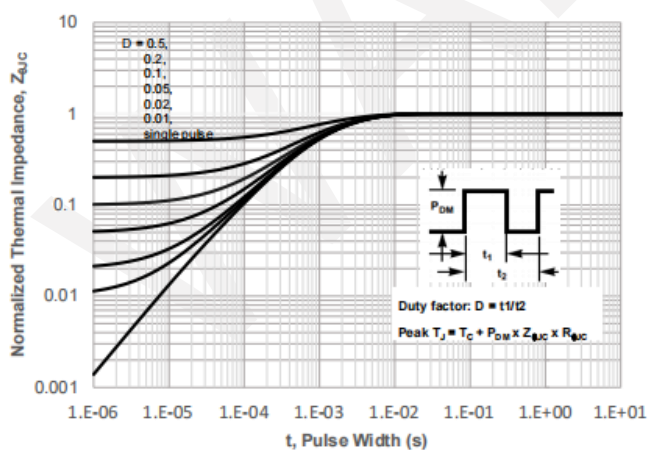
Normalized on Resistance vs.
Junction Temperature



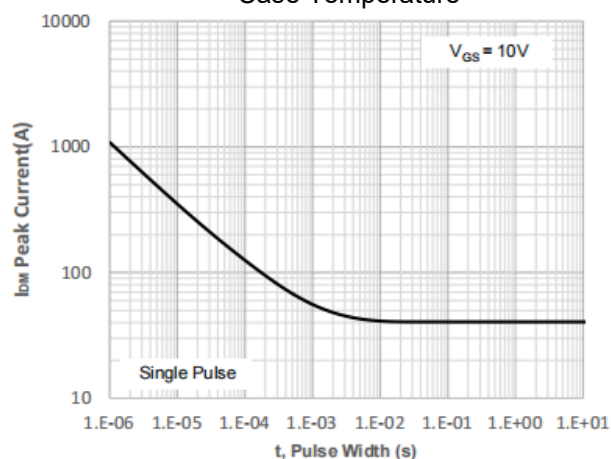
Maximum Safe Operating Area



Maximum Continuous Drain Current vs.
Case Temperature

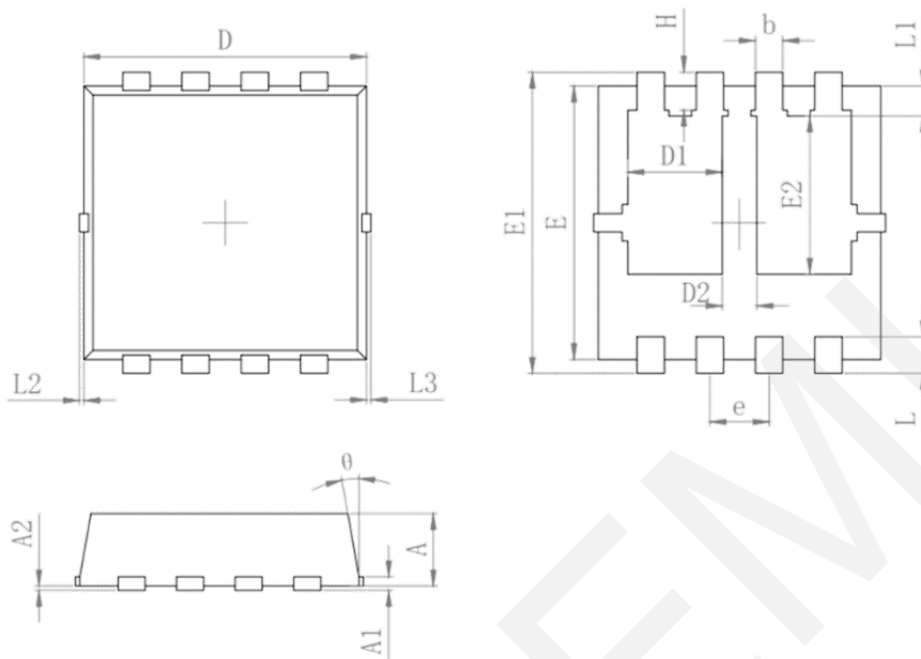


Normalized Maximum Transient
Thermal Impedance



Peak Current Capacity

8.Package Dimensions



SYMBOL	MILLIMETER	
	MIN	MAX
A	0.700	0.900
A1	0.152 REF.	
A2	0~0.05	
D	3.000	3.200
D1	0.935	1.135
D2	0.280	0.480
E	2.900	3.100
E1	3.150	3.450
E2	1.535	1.935
b	0.200	0.400
e	0.550	0.750
L	0.300	0.500
L1	0.180	0.480
L2	0~0.100	
L3	0~0.100	
H	0.315	0.515
θ	8°	12°

9. Important Notice

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